

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph on page 91, line , to page , line , as follows:

Next, the method of cleaning with this cleaning apparatus will be described. First, the semiconductor substrate W is horizontally rotated integrally with the substrate holding portion 222, with the substrate being held horizontally by the spin chucks 221 of the substrate holding portion 222. In this state, an acid solution is supplied from the center nozzle 224 to the central portion of the face of the substrate W. The acid solution may be a non-oxidizing acid, and hydrofluoric acid, hydrochloric acid, sulfuric acid, citric acid, oxalic acid, or the like is used. On the other hand, an oxidizing agent solution is supplied continuously or intermittently from the edge nozzle 226 to the peripheral edge portion of the substrate W. As the oxidizing agent solution, one of an aqueous solution of ozone, an aqueous solution of hydrogen peroxide, ~~an aqueous solution of nitric acid,~~ and an aqueous solution of sodium hypochlorite is used, or a combination of these is used.